

### INCHANGE SEMICONDUCTOR

# isc N-Channel MOSFET Transistor

# SPW11N60S5

## ISPW11N60S5

### • FEATURES

- Static drain-source on-resistance:  $R_{DS}(on) \leqslant 380 m_{\Omega}$
- · Enhancement mode:
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

### DESCRITION

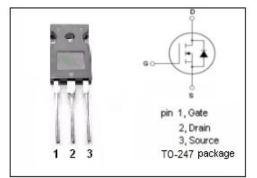
Improved transconductance

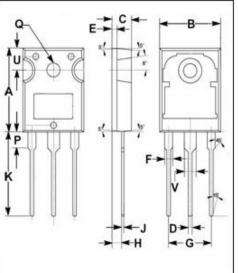
### • ABSOLUTE MAXIMUM RATINGS(Ta=25°C)

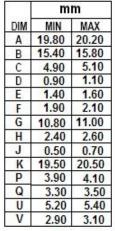
PARAMETER	VALUE	UNIT
Drain-Source Voltage	600	V
Gate-Source Voltage	±20	V
Drain Current-Continuous	11	А
Drain Current-Single Pulsed 22		А
Total Dissipation @T₀=25℃	125	W
Max. Operating Junction Temperature	150	°C
Storage Temperature	-55~150	°C
	Drain-Source Voltage   Gate-Source Voltage   Drain Current-Continuous   Drain Current-Single Pulsed   Total Dissipation @Tc=25°C   Max. Operating Junction Temperature	Drain-Source Voltage600Gate-Source Voltage±20Drain Current-Continuous11Drain Current-Single Pulsed22Total Dissipation @Tc=25°C125Max. Operating Junction Temperature150

#### THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	МАХ	UNIT	
Rth(j-c)	Channel-to-case thermal resistance	1	°C/W	
Rth(j-a)	Channel-to-ambient thermal resistance	62	℃/W	









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### **ELECTRICAL CHARACTERISTICS**

#### $T_{\text{C}}\text{=}25^\circ\!\!\mathbb{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	ТҮР	МАХ	UNIT
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V; I <sub>D</sub> =0.25mA	600			V
$V_{GS(th)}$	Gate Threshold Voltage	VDS=VGS; ID=0.5mA	3.5		5.5	V
$R_{\text{DS(on)}}$	Drain-Source On-Resistance	V <sub>GS</sub> =10V; I <sub>D</sub> =7A			380	mΩ
I <sub>GSS</sub>	Gate-Source Leakage Current	V <sub>GS</sub> = 30V; V <sub>DS</sub> = 0V			0.1	μ Α
I <sub>DSS</sub>	Drain-Source Leakage Current	V <sub>DS</sub> =600V; V <sub>GS</sub> = 0V			25	μA
V <sub>SD</sub>	Diode forward voltage	I <sub>F</sub> =IS, V <sub>GS</sub> = 0V			1.2	V

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